

SEMICONDUCTOR

# BC214LB

### **PNP General Purpose Amplifier**

- This device is deisgned for use as general purpose amplifiers and switches requiring collector currents to 300mA.
- Sourced from process 68.



1. Emitter 2. Collector 3. Base

## Absolute Maximum Ratings\* Ta=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CEO</sub>	Collector-Emitter Voltage	-30	V
V <sub>CBO</sub>	Collector-Base Voltage	-45	V
V <sub>EBO</sub>	Emitter-Base Voltage	-5.0	V
I <sub>C</sub>	Collector Current (DC) Continuous	-500	mA
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature Range	- 55 ~ 150	°C

\* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

#### NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations

### Electrical Characteristics Ta=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
Off Characte	eristics				
V <sub>(BR)CEO</sub>	Collector-Emitter Voltage	$I_{\rm C} = -2mA, I_{\rm B} = 0$	-30		V
V <sub>(BR)CBO</sub>	Collector-Base Voltage	$I_{\rm C} = -10 \mu {\rm A}, \ I_{\rm E} = 0$	-45		V
V <sub>(BR)EBO</sub>	Emitter-Base Voltage	$I_{\rm E} = -10\mu A, I_{\rm C} = 0$	-5.0		V
I <sub>CBO</sub>	Collector Cut-off Current	$V_{CB} = -30V, I_E = 0$		-15	nA
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB} = -4V, I_{C} = 0$		-15	nA
On Characte	eristics *				
h <sub>FE</sub>	DC Current Gain	$V_{CE} = -5V, I_{C} = -2mA$	140	400	
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	$I_{C} = -10$ mA, $I_{B} = -0.5$ mA $I_{C} = -100$ mA, $I_{B} = -5$ mA		-0.25 -0.6	V
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage	$I_{\rm C} = -100$ mA, $I_{\rm B} = -5$ mA		-1.1	V
V <sub>BF</sub> (on)	Base-Emitter On Voltage	$V_{CF} = -5V, I_{C} = -2mA$	-0.6	-0.72	V
Small Signa	I Characteristics		I		
f <sub>T</sub>	Current gain Bandwidth Product	$V_{CE} = -5V, I_{C} = -10mA$ f = 100MHz	200		MHz
NF	Noise Figure	$V_{CE} = -5V$ , $I_C = -200\mu A$ $R_G = 2k\Omega$ , f = 15.7KHz		2.0	dB
h <sub>fe</sub>	Small Signal Current Gain	$I_{C} = -2mA, V_{CE} = -5V$ f = 1KHz	200	400	
C <sub>OB</sub>	Output Capacitance	V <sub>CB</sub> = -10V, f = 1MHz		10	pF

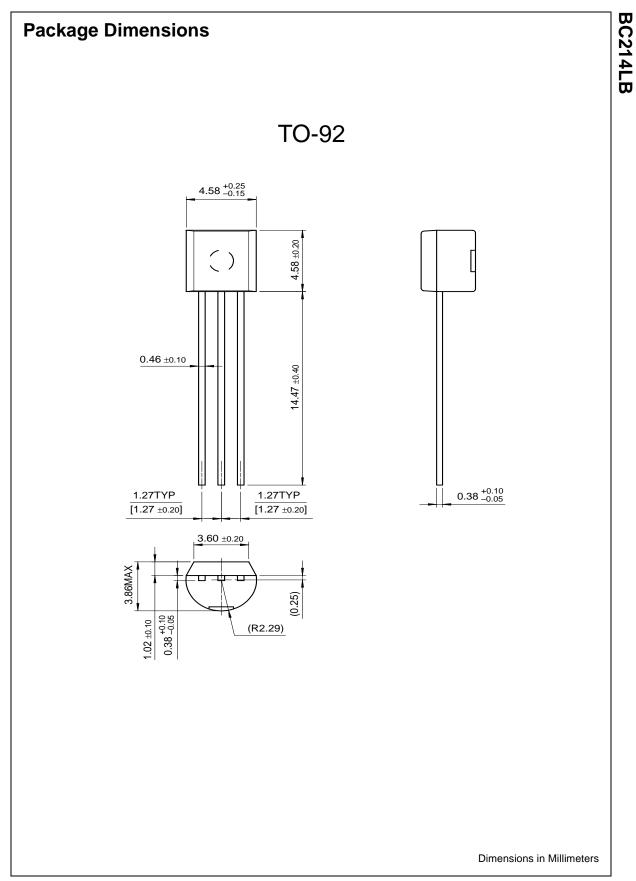
Pulse Test: Pulse Width  $\leq 300 \mu s, \, Duty \, Cycle \leq 2.0\%$ 

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Symbol	Parameter	Max.	Units
D	Total Device Dissipation	625	mW
	Derate above 25°C	5.0	mW/°C
$R_{ extsf{ heta}JC}$	Thermal Resistance, Junction to Case	83.3	°C/W
R <sub>0JA</sub>	Thermal Resistance, Junction to Ambient	200	°C/W

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Programmable A	ctive Droop™	POP™	SuperSOT™-3	

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